

**Silicon Carbide Schottky Barrier Diode**

**Reverse Voltage - 650 V**

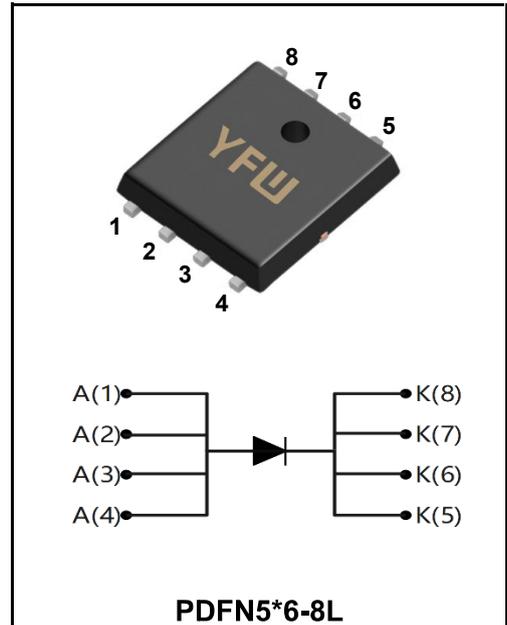
**Forward Current - 4 A**

**DESCRIPTION**

- ◆650V Schottky diode
- ◆Zero reverse recovery current
- ◆Zero forward recovery voltage
- ◆High frequency operation
- ◆Switching characteristics independent of temperature Fast switch
- ◆Positive temperature coefficient of forward voltage ( $V_F$ )

**APPLICATION**

- ◆Switch mode power supplies(SMPS)
- ◆Boost diodes in PFC or DC/DC stages
- ◆Free wheeling diodes in inverter stages AC/DC converters



**Absolute Maximum Ratings**

(Rating at 25°C junction temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	$V_{RRM}$	650	V
Maximum DC blocking voltage	$V_{DC}$	650	V
Average forward current	$I_{F(AV)}$	4	A
Repetitive Peak Surge Current Half Sine Wave, D=0.1	$I_{FRM}$	$t_p=10ms, T_c=25^\circ C$	20
		$t_p=10ms, T_c=125^\circ C$	16
Peak Forward Surge Current Half Sine Wave	$I_{FSM}$	$t_p=10ms, T_c=25^\circ C$	20
		$t_p=10ms, T_c=125^\circ C$	16
Peak Forward Surge Current $t_p = 10\mu s$ , Pulse	$I_{FSM}$	280	A
Maximum Power Dissipation	$P_{total}$	46	W
Operating Junction Temperature Range	$T_j$	-55 to +175	°C
Storage Temperature Range	$T_{stg}$	-55 to +175	°C

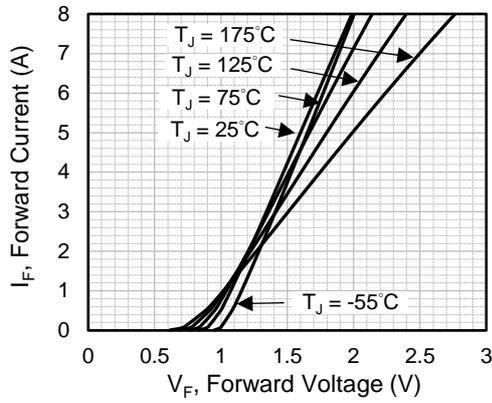
**Electrical Characteristics**

(Rating at 25°C junction temperature unless otherwise specified.)

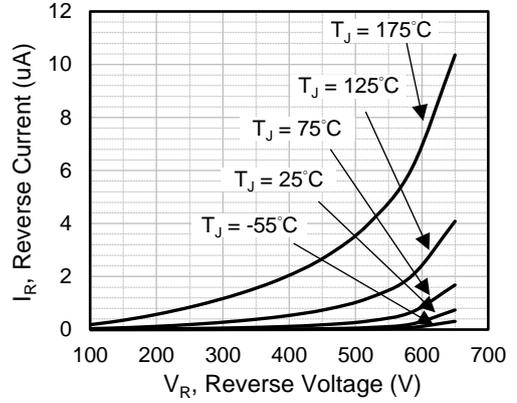
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=4A, T_J=25^\circ C$	$V_F$	-	1.5	1.7	V
	$I_F=4A, T_J=175^\circ C$		-	1.8	-	
Reverse Leakage Current	$V_R=650V, T_J=25^\circ C$	$I_R$	-	2	40	$\mu A$
	$V_R=650V, T_J=175^\circ C$		-	0.02	-	mA
Total capacitance charge	$I_F=4A, V_R=400V$	$Q_C$	-	6.4	-	nC
Total capacitance	$V_R=1V, f=1MHz$	$C$	-	146	-	pF
	$V_R=200V, f=1MHz$		-	9.9	-	
	$V_R=400V, f=1MHz$		-	6.2	-	
Capacitance stored energy	$V_R=400V$	$E_C$	-	0.8	-	$\mu J$
Thermal Resistance		$R_{\theta JC}$	-	3.26	-	$^\circ C/W$

Characteristics Curve

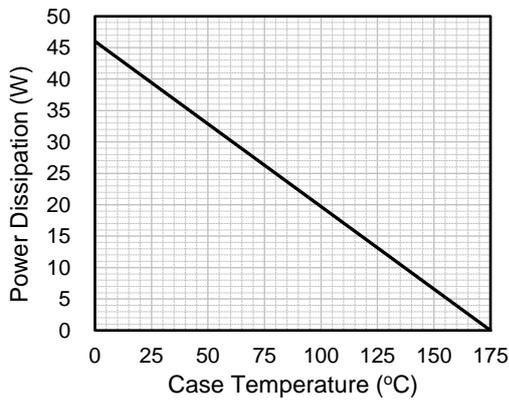
**Fig.1 Forward Characteristics**



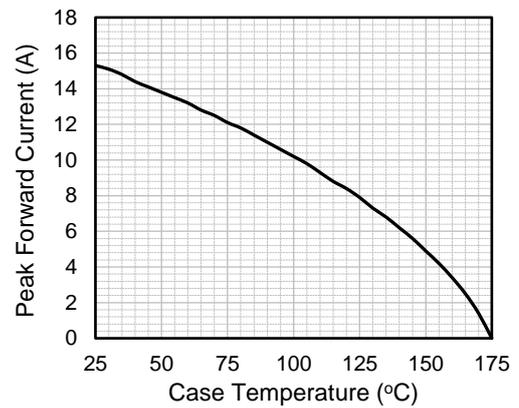
**Fig.2 Reverse Characteristics**



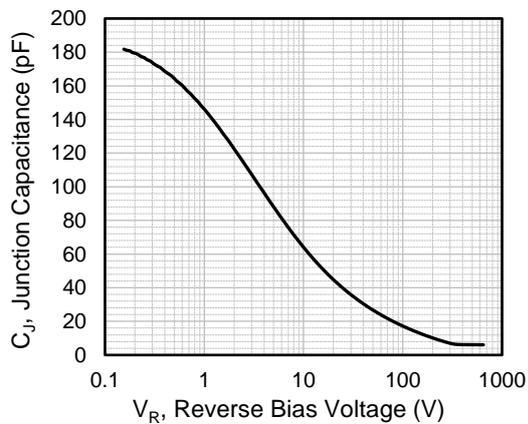
**Fig.3 Power Derating Curve**



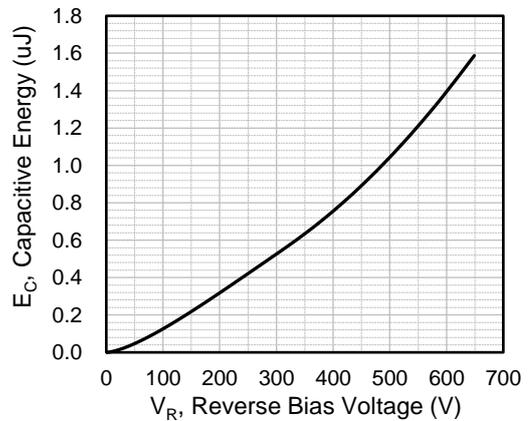
**Fig.4 Current Derating Curve**



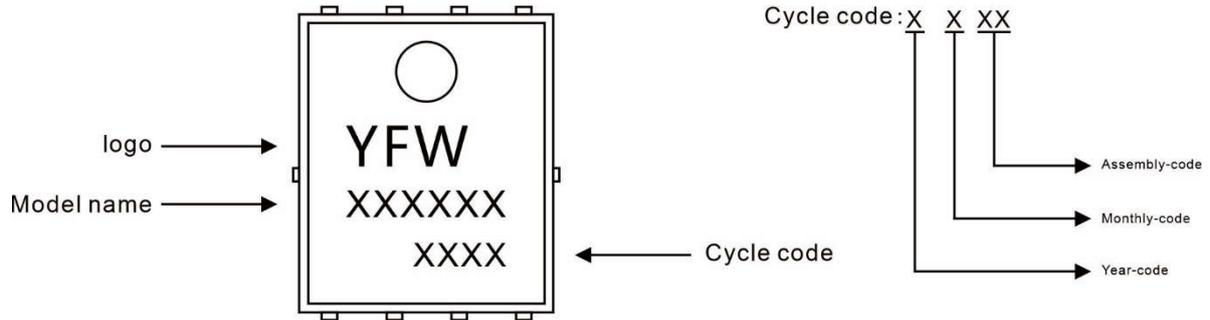
**Fig.5 Typical Junction Capacitance**



**Fig.6 Capacitance Stored Energy**



**Marking Diagram**



**Ordering information**

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFWD304065NT	PDFN5*6-8L	0.0032oz(0.093g)	5000pcs/reel	10000pcs/box 50000pcs/Carton

**Package Dimensions**

PDFN5\*6-8L

Dim	Millimeter		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.2	35	45
A2	0.204	0.304	8	12
b	0.4ref.		16ref.	
b1	0.2	0.4	8	16
D	5.0	5.3	197	209
D1	4.84	5.24	191	206
E	5.95	6.35	234	250
E1	3.275	3.675	129	145
E2	5.69	6.09	224	232
e	1.27typ.		50typ.	
K	1.29typ.		51typ.	
L	0.585	0.785	23	27
L1	0.7typ.		28typ.	

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